

Pro Electron Surface Mount Bipolar Devices (continued)

Device No. (SOT-23 Mark)	Case Style	V _{CES} [*]		V _{CEO}		V _{EBO}		I _{CES} [*]		I _{hFE}		I _C & V _{CE}		V _{CE(SAT)} (V) & V _{BE(SAT)} (V)		I _C (mA)		C _{ob} (pF)		f _T (MHz)		I _C (mA)	NF (dB) Max	Test Conditions	Process No.
		V _{CBO} (V) Min	V _{CE0} (V) Min	V _{CE0} (V) Min	V _{EBO} (V) Min	I _{CBO} (nA) Max	I _{hFE} Min	I _{hFE} Max	I _C (mA) Max	V _{CE} (V) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	V _{BE(SAT)} (V) Max	I _C (mA) Min	I _C (mA) Max	Max	Min	Max	Max						
BC859C (4C)	TO-236 (49)	30	30	5	30	15	30	420	800	2	5	0.65	100									4	(Note 1)	68	
BC860C (4G)	TO-236 (49)	50	45	5	30	15	30	420	800	2	5	0.3 0.65	10 100									3	(Note 1)	68	
BCP52	TO-261 (47)	60	60	5	30	100	30	25 40	250 150	2	2	0.5	*1 500											78 (6-28)	
BCP63	TO-261 (47)	100	80	5	30	100	30	25 40	250 150	2	2	0.5	*1 500											78	
BCP54	TO-261 (47)	45	45	5	30	100	30	25 40	250 150	2	2	0.5	*1 500											38 (6-32)	
BCP55	TO-261 (47)	60	60	5	30	100	30	25 40	250 150	2	2	0.5	*1 500											38	
BCP56	TO-261 (47)	100	80	5	30	100	30	25 40	250 150	2	2	0.5	*1 500											38	
BCV26 (FD)	TO-236 (49)	40	30	10	30	100	30	4,000 10,000 20,000	1 10 100	5 5 5	5	1	1.5 100											61 (6-35)	
BCV27 (FF)	TO-236 (49)	40	30	10	30	100	30	4,000 10,000 20,000	1 10 100	5 5 5	5	1	1.5 100											05 (6-39)	
BCV71 (KT)	TO-236 (49)	80	60	5	20	100	20	110	220	2	5	0.25	10									10	(Note 1)	10	
BCV72 (K8)	TO-236 (49)	80	60	5	20	100	20	200	450	2	5	0.25	10									10	(Note 1)	10	
BCW30 (C2)	TO-236 (49)	32	32	5	32	100	32	215	500	0.01 2	5 5	0.3	10									10	(Note 1)	68	
BCW31 (D1)	TO-236 (49)	32	32	5	32	100	32	150	270	0.01 2	5 5	0.25	10									10	(Note 1)	10	

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (section-page) of device datasheet.